

Development of silicon oxynitride nanocomposites with single-walled carbon nanotubes as protective coatings for solar cells = Üheseinaliste süsiniknanotorudega ränioksiidist nanokomposiitmaterjalide arendamine päikesepatareide kaitsekattedeks

Shmagina, Elizaveta 2025 https://www.ester.ee/record=b5739646*est <https://digikogu.taltech.ee/et/Item/5b38d0d4-d585-496f-b18e-de06aae6a6da> <https://doi.org/10.23658/taltech.20/2025>

A DLTS study of 4H-SiC-based p-n junctions fabricated by boron implantation

Ivanov, Pavel; Potapov, Alexander; Samsonova, Tatyana; **Korolkov, Oleg; Sleptšuk, Natalja** Semiconductors 2011 / p. 1306-1310 : ill <https://doi.org/10.1134/S1063782611100101>

Impurity interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Medvid, A. Materials science and engineering : B 2006 / p. 222-226 : ill <https://www.sciencedirect.com/science/article/pii/S0921510706004375>

Investigation of strain relaxation mechanism in Si-SiO₂ system during the process of its formation

Kropman, Daniel; Poll, V.; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn**; Arbu, Uno; Paomets, V. Physica status solidi (a) 2003 / 2, p. 297-301 <https://onlinelibrary.wiley.com/doi/abs/10.1002/pssa.200306611>

Simulations of wide bandgap SiC N-N heterostructure diode

Patankar, Udayan Sunil; Koel, Ants; Pardy, Tamas 2020 IEEE International Conference on Consumer Electronics (ICCE), Las Vegas, NV, USA, January 4-6, 2020 2020 / 4 p <https://doi.org/10.1109/ICCE46568.2020.9043130>

Strain relaxation mechanism in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Öpik, Andres; Lott, Kalju; Volobujeva, Olga; Kärner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A. Radiation Interaction with Materials and its use in Technologies : Kaunas, 24-27.09.2008 2008 / p. 204-207 <https://www.sciencedirect.com/science/article/pii/S0921452609010321>

Stress relaxation mechanism by strain in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksa, Edvins Solid state phenomena 2011 / p. 259-262 https://globaljournals.org/GJSFR_Volume17/1-Stresses-Relaxation-Mechanism.pdf

Structure-reactivity relationships for organosilicon compounds revisited

Ploom, Anu; Tuulmets, Ants ISOS XVII Berlin 2014 : the 17th International Symposium on Silicon Chemistry jointly with the 7th European Silicon Days : Berlin, August 3-8, 2014 2014

Structure-reactivity relationships in organosilicon chemistry revisited

Ploom, Anu; Tuulmets, Ants; Järv, Jaak Central European journal of chemistry 2011 / p. 2910-2916 <https://link.springer.com/article/10.2478/s11532-011-0075-x>

Зависимость между содержанием P₂O₅ и SiO₂ в оболочках фосфоритов

Veiderma, Mihkel Сборник статей по химии и химической технологии. 10 1964 / с. 299-304 : илл https://www.ester.ee/record=b2181961*est <https://digikogu.taltech.ee/et/Item/9569e6db-150a-42c8-bf3b-765725dfd969>

Создание и свойства высокоомных эпитаксиальных слоев кремния большой площади

Vinnal, J.A.; **Kõverik, Kait**; Tarma, M. Тезисы докладов республиканской научно-технической конференции, посвященной 80-летию со дня изобретения радио А. С. Поповым 1975 / с. 3 https://www.ester.ee/record=b1322122*est